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APPLICATION N	Ю.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/766,277		01/27/2004	Decai Sun	LUM-03-06-01	3462
32566	7590	05/04/2005		EXAMINER	
		GROUP LLP	SOWARD, IDA M		
2635 NO SUITE 22		ST STREET		ART UNIT	PAPER NUMBER
SAN JOSE, CA 95134				2822	
				DATE MAILED: 05/04/2009	ς .

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	10/766,277	SUN, DECAI	
Office Action Summary	Examiner	Art Unit	
	lda M. Soward	2822	
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet wit	h the correspondence address	S
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a rep - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailir earned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply within the statutory minimum of thirty will apply and will expire SIX (6) MONT i.e., cause the application to become ABA	ply be timely filed (30) days will be considered timely. HS from the mailing date of this communance ANDONED (35 U.S.C. § 133).	nication.
Status			
1) Responsive to communication(s) filed on 27 J	lanuary 2004.		
2a) This action is FINAL . 2b) ⊠ This	s action is non-final.		
3) Since this application is in condition for allowa	·	·	rits is
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.	
Disposition of Claims			
 4) Claim(s) 1-19 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) Claim(s) is/are allowed. 6) Claim(s) 1,2,14 and 17 is/are rejected. 7) Claim(s) 3-13,15,16,18 and 19 is/are objected. 8) Claim(s) are subject to restriction and/o 	awn from consideration.		
Application Papers	· ·		
9) The specification is objected to by the Examine	er.		
10)⊠ The drawing(s) filed on <u>27 January 2004</u> is/are	e: a)□ accepted or b)⊠ ob	jected to by the Examiner.	
Applicant may not request that any objection to the	•	• •	
Replacement drawing sheet(s) including the correct	•	· •	• •
11) The oath or declaration is objected to by the E	xaminer. Note the attached	Office Action or form PTO-15	02.
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau	ts have been received. ts have been received in Ap prity documents have been r nu (PCT Rule 17.2(a)).	oplication No received in this National Stag	e
* See the attached detailed Office action for a list	t of the certified copies not r	eceived.	
Attachment(s)			
Notice of References Cited (PTO-892)	4) 🔲 Interview Su	ımmary (PTO-413)	
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 1-27-04 	Paper No(s)	/Mail Date formal Patent Application (PTO-152)	,

DETAILED ACTION

This Office Action is in response to the application filed January 27, 2004.

Drawings

The drawings are objected to as failing to comply with 37 CFR 1.84(p)(4) because reference character:

- "9C" has been used to designate both thick contact layer and semiconductor layer under reflector in paragraph [0015] of page 4;
- "10C" has been used to designate both semiconductor layer under reflector, large reflective sheet and under reflective sheet in paragraphs [0016] and [0017] of page 4; and
- 3. "4" has been used to designate both **highly doped layers** and **heavily**doped layers in paragraph [0017] of page 4.

Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of

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any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-2 and 14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ludowise (US 2005/0045893 A1) in view of Cho et al. (5,226,053).

Ludowise teaches a semiconductor light emitting device comprising: a light emitting region 6 disposed between a region 7 of first conductivity type and a region 5 of second conductivity type (abstract, page 1, paragraph [0007], Figure 1A, page 1, paragraph [0020]).

However, Ludowise fails to teach at least one heavily doped layer disposed within the region of first conductivity type, wherein the heavily doped layer is more heavily doped than the region of first conductivity type.

Cho et al. teach at least one heavily doped layer 12 disposed within the region of first conductivity type 12-14, wherein the heavily doped layer 12 is more heavily doped than the region of first conductivity type 13-14 (Figure 1, column 7, lines 47-66).

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor light emitting device

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structure as taught by Ludowise with the semiconductor light emitting device having at

least one heavily doped layer disposed within the region of first conductivity type,

wherein the heavily doped layer is more heavily doped than the region of first

conductivity type as taught by Cho et al. to provide a semiconductor light emitting

device with improved light emitting characteristics suitable for optical fiber

communication (column 2, lines 41-43).

In regard to claim 2, Ludowise teaches the light emitting region comprising at

least one layer of InGaP (page 2, paragraph [0020]).

In regard to claim 14, Ludowise teaches the region 7 of first conductivity type and

the region 5 of second conductivity type are cladding layers adjacent to the active

region 6, the device further comprising: a contact region 8 of first conductivity type

adjacent to a surface of the cladding layer 7 of first conductivity type opposite the active

region 6 (Figure 1A); and a contact region 3 of second conductivity type adjacent to a

surface of the cladding layer 5 of second conductivity type opposite the active region

(Figure 5) (page 2, paragraph [0020]).

Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over

Ludowise (US 2005/0045893 A1) as applied to claims 1-2 and 14 above, and further in

view of Cho et al. (5,226,053).

Ludowise teaches all mentioned in the rejection above.

However, Ludowise fails to teach the region 12 of first conductivity type and the

region 17 of second conductivity type are contact regions; the contact region 12 of first

conductivity type is spaced apart from the active region 15 by a cladding region 14 of first conductivity type; and the contact region 17 of second conductivity type is spaced apart from the active region by a cladding region 16 of second conductivity type (Figure 3, column 7, lines 54-66).

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor light emitting device structure as taught by Ludowise with the semiconductor light emitting device having the region of first conductivity type and the region of second conductivity type are contact regions; the contact region of first conductivity type is spaced apart from the active region by a cladding region of first conductivity type; and the contact region of second conductivity type is spaced apart from the active region by a cladding region of second conductivity type as taught by Cho et al. to design light emitting device with improved light emitting characteristics (column 2, lines 41-43).

Allowable Subject Matter

Claims 3-13, 15-16 and 18-19 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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The following patents are cited to further show the state of the art with respect to semiconductor light emitting devices:

Guido (5,614,734) Khare et al. (US 2003/0205717 A1)

Kish, Jr. et al. (6,015,719) Lebby et al. (5,498,883)

Lee et al. (US 6, 720,570 B2) Trussell, Jr. et al. (4,371,968)

Ueda (US 2003/0089906 A1).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ida M. Soward whose telephone number is 571-272-1845. The examiner can normally be reached on Monday - Thursday 6:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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